

**SANYO****DTN8**

Silicon Diffused Junction Type

**8A Bidirectional Thyristor****Features**

- AC power control.
- Peak OFF-state voltage : 400, 600V.
- RMS ON-state current : 8A.

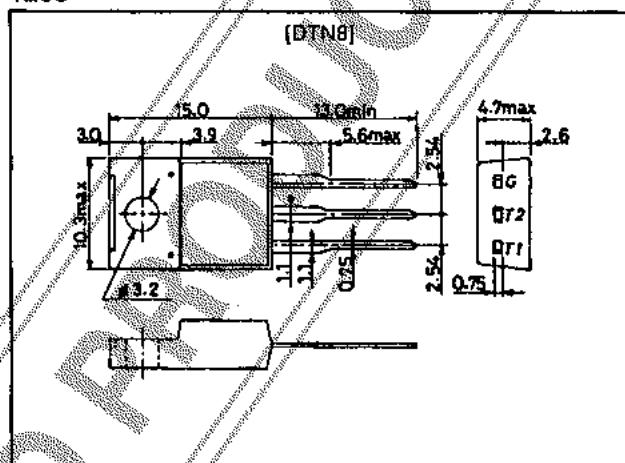
\* : The gate trigger modes are shown below.

Trigger mode	T2	T1	G
I	+	-	+
II	+	-	-
III	-	+	+
IV	-	+	-

**Package Dimensions**

unit:mm

1263

**Specifications****Absolute Maximum Ratings at Ta = 25°C**

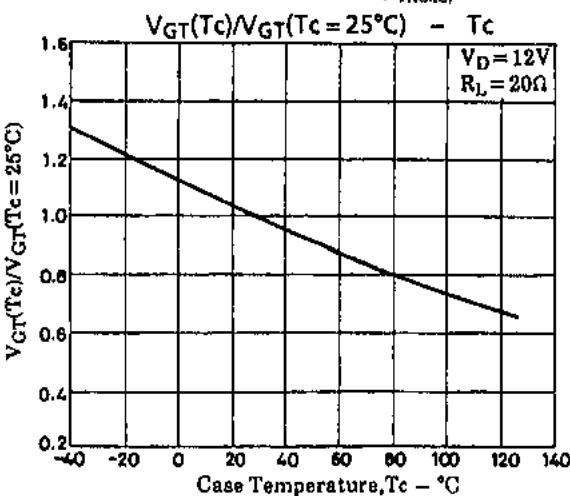
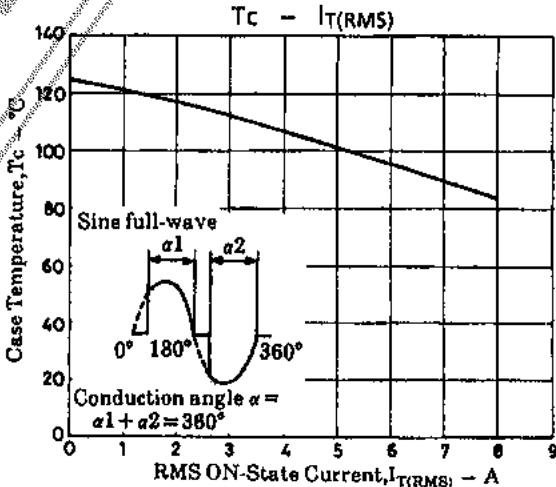
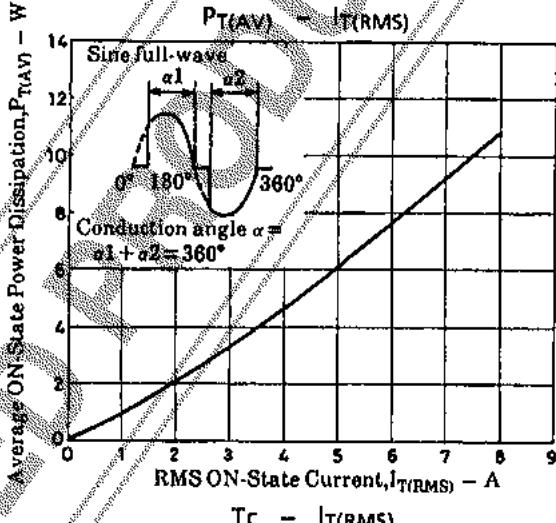
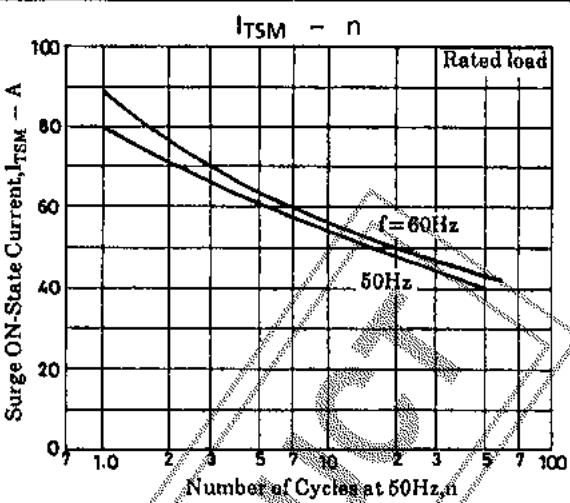
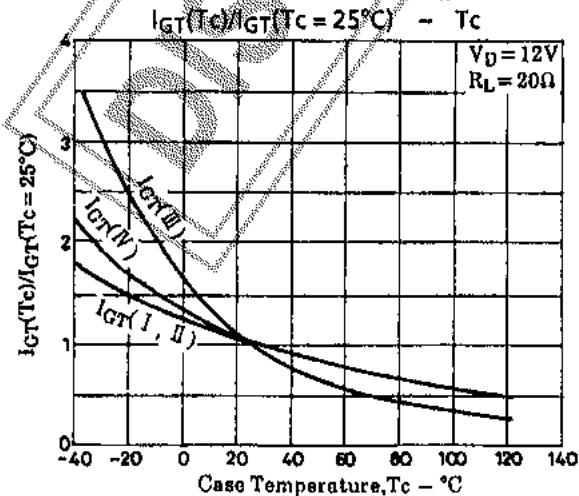
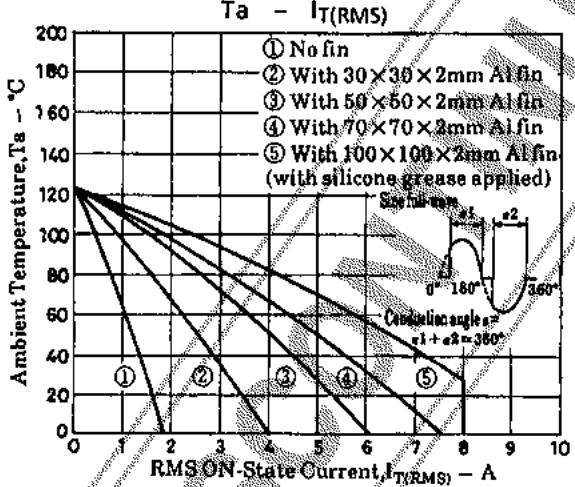
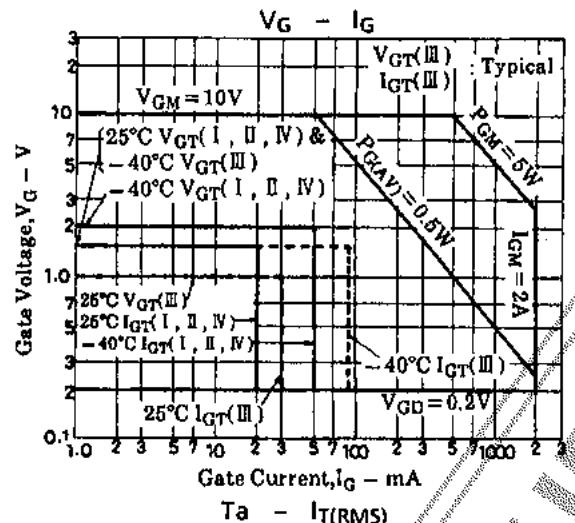
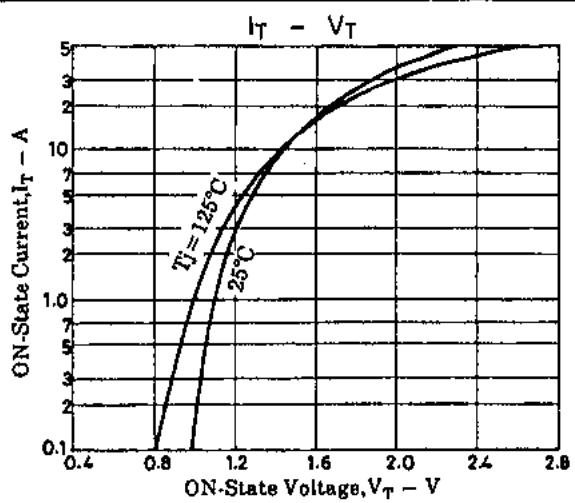
Parameter	Symbol	Conditions	DTN8E	DTN8G	Unit
Repetitive Peak OFF-State Voltage	V <sub>DRM</sub>		400	600	V
RMS ON-State Current	I <sub>T(RMS)</sub>	Single-phase full-wave, T <sub>c</sub> =83°C	→	8	A
Surge ON-State Current	I <sub>TSM</sub>	Peak 1 cycle, 50Hz	→	80	A
Amperes Squared-Seconds	(I <sub>T</sub> ·dt)	t <sub>max</sub> ≤10ms	→	32	A <sup>2</sup> s
Critical Rate of Rise of ON-State Current	dI <sub>T</sub> /dt		→	50	A/μs
Peak Gate Power Dissipation	P <sub>GM</sub>		→	5	W
Average Gate Power Dissipation	P <sub>G(AV)</sub>		→	0.5	W
Peak Gate Forward Current	I <sub>GM</sub>		→	±2	A
Peak Gate Forward Voltage	V <sub>GM</sub>		→	±10	V
Junction Temperature	T <sub>j</sub>		→	125	°C
Storage Temperature	T <sub>stg</sub>		→	-40 to +125	°C
Weight			→	1.7	g

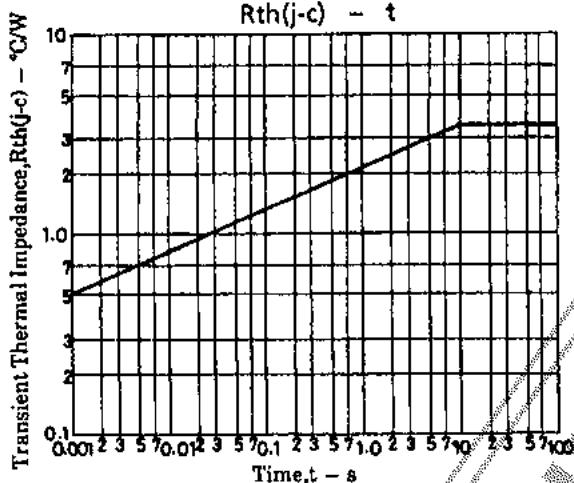
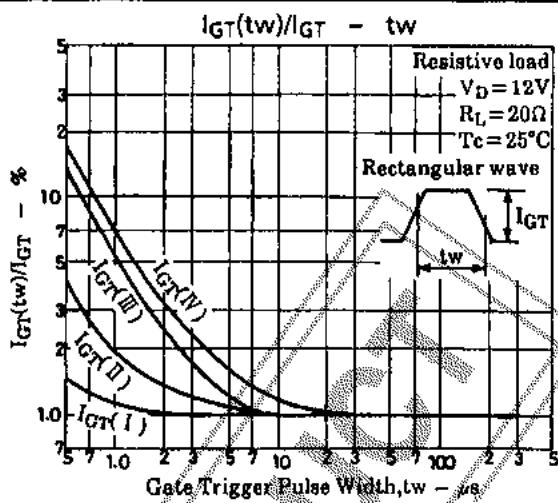
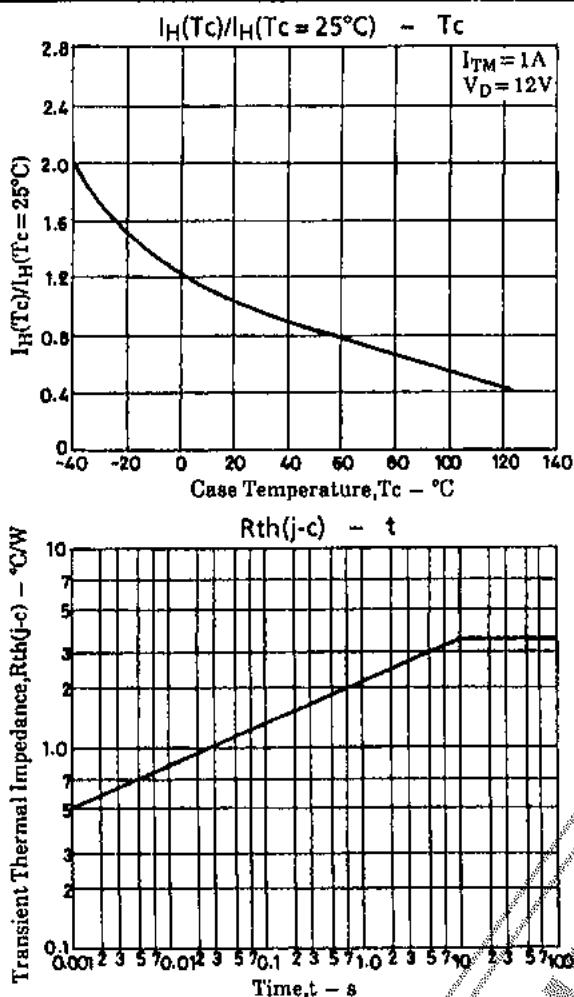
**Electrical Characteristics at Ta = 25°C**

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Repetitive Peak OFF-State Current	I <sub>DRM</sub>	V <sub>D</sub> =V <sub>DRM</sub>			20	μA
Peak ON-State Voltage	V <sub>TM</sub>	I <sub>TM</sub> =12A			1.5	V
Critical Rate of Rise of Commutating OFF-State Voltage	(dv/dt)C	V <sub>D</sub> =400V, T <sub>j</sub> =125°C	4			V/μs
Holding Current	I <sub>H</sub>	I <sub>TM</sub> =1A, V <sub>D</sub> =12V			50	mA
Gate Trigger Current (I)	I <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =20Ω			20	mA
Gate Trigger Current (II)	I <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =20Ω			20	mA
Gate Trigger Current (III)	I <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =20Ω	30			mA
Gate Trigger Current (IV)	I <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =20Ω			20	mA
Gate Trigger Voltage (I)	V <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =20Ω			1.5	V
Gate Trigger Voltage (II)	V <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =20Ω			1.5	V
Gate Trigger Voltage (III)	V <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =20Ω	1.0			V
Gate Trigger Voltage (IV)	V <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =20Ω			1.5	V
Gate Nontrigger Voltage	V <sub>GD</sub>	T <sub>c</sub> =125°C, V <sub>D</sub> =V <sub>DRM</sub>	0.2			V
Thermal Resistance	R <sub>th(j-c)</sub>	AC			3.6	°C/W

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